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(54) **POWER TRANSMISSION GATE USING CHARGE PUMP**

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(71) Applicant: **Murata Manufacturing Co., Ltd.**,
Kyoto (JP)

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(72) Inventors: **Aaron COOK**, Windham, NH (US);
David J. PERREAULT, Cambridge,
MA (US); **John R. HOVERSTEN**,
Arlington, MA (US)

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(73) Assignee: **Murata Manufacturing Co., Ltd.**,
Kyoto (JP)

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(57) **ABSTRACT**

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Described is a power transmission gate which includes a charge pump, an NMOS transistor, and a gate driver circuit configured to power (or bias or “drive”) a gate of the NMOS transistor. With this arrangement, a power transmission gate capable of achieving substantially the same resistance provided by prior art power transmission gates while having a footprint of just over one NMOS size unit is provided.

